

Preliminary Amendment  
Divisional of USSN 09/882,892  
February 26, 2004  
Page 5

**AMENDMENTS TO THE ABSTRACT**

Please insert the following Abstract after the last page of claims in the subject application:

**ABSTRACT**

A permanently-ON MOS transistor comprises silicon source and drain regions of a first conductivity type in a silicon well region of a second conductivity type. A silicon contact region of the first conductivity types is buried in the well region, said contact region contacting said source region and said drain region. A first gate insulating layer is selectively placed over the silicon source and drain regions. A second gate insulating layer is selectively placed over the first gate insulating layer and over the silicon contact region. A polysilicon gate region is placed over the second gate insulating layer.